

**Silicon NPN Power Transistor**

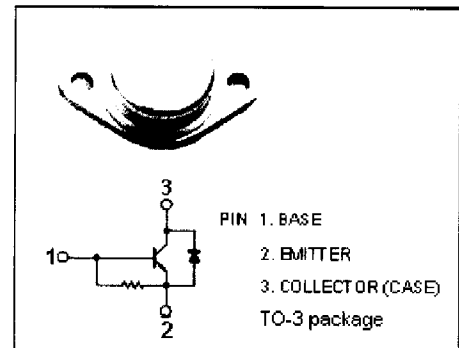
**BU607D**

**DESCRIPTION**

- High Voltage:  $V_{CEV} = 330V(\text{Min})$
- Fast Switching Speed-  
:  $t_f = 0.75 \mu s(\text{Max})$
- Low Saturation Voltage-  
:  $V_{CE(\text{sat})} = 1.0V(\text{Max}) @ I_C = 5A$

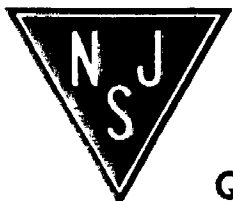
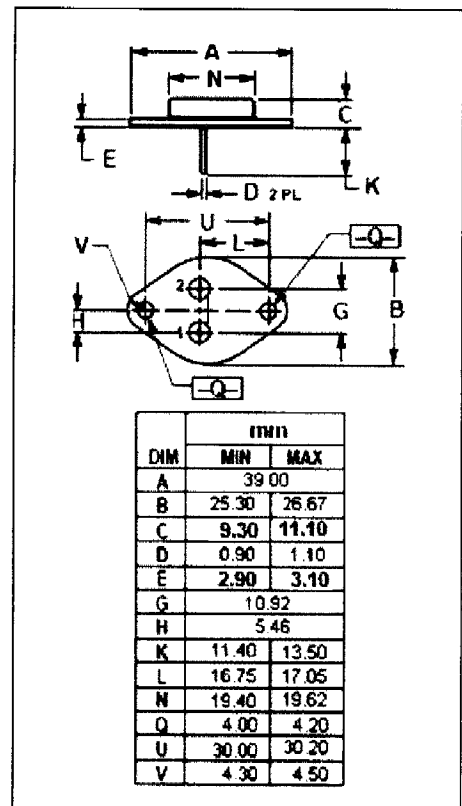
**APPLICATIONS**

- Designed for use in horizontal deflection output stages of TV's and CRT's



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	330	V
$V_{CEV}$	Collector-Emitter Voltage	330	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	7	A
$I_{CM}$	Collector Current-Peak	10	A
$I_B$	Base Current	4	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{\text{stg}}$	Storage Temperature Range	-65~150	$^\circ\text{C}$



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## BU607D

### ELECTRICAL CHARACTERISTICS

$T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.65\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.65\text{A}$			1.3	V
$h_{FE}$	DC Current Gain	$I_C=2\text{A}; V_{CE}=5\text{V}$		15		
$I_{CEV}$	Collector Cutoff Current	$V_{CE}=330\text{V}; V_{BE}=-1.5\text{V}$			15	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			400	mA
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=10\text{V}; f_{test}=1\text{MHz}$	10			MHz
$V_{ECF}$	C-E Diode Forward Voltage	$I_F=5\text{A}$			1.5	V
$t_f$	Fall Time	$I_C=5\text{A}; I_{B1}=-I_{B2}=0.65\text{A}; V_{CC}=40\text{V}$			0.75	$\mu\text{s}$